

Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in this application.

Listing of Claims:

Claim 1 (Previously Presented): A semiconductor memory element comprising:
a substrate;
a semiconductor circuit portion comprising an organic semiconductor disposed on the substrate; and
a protection portion disposed adjacent to the semiconductor circuit portion, the protection portion being made of a material in which a crack extending to the semiconductor circuit portion is formed after a predetermined means performs.

Claim 2 (Previously Presented): A semiconductor memory element comprising:
a substrate;
a semiconductor circuit portion comprising an organic semiconductor disposed on the substrate;
a protection portion disposed adjacent to the semiconductor circuit portion and including a window portion; and
a strippable seal member for sealing the window portion of the protection portion.

Claim 3 (Previously Presented): A semiconductor memory element comprising:
a substrate;
a semiconductor circuit portion comprising an organic semiconductor disposed on the substrate;
a protection portion disposed adjacent to the semiconductor circuit portion; and
a performance deterioration portion including a performance deterioration material for deteriorating a performance of the organic semiconductor and disposed adjacent to the protection

portion, the protection portion being made of a material in which a crack extending to the semiconductor circuit portion is formed after a predetermined means performs.

Claim 4 (Previously Presented): The semiconductor memory element according to claim 1, wherein the predetermined means is a mechanical punch means.

Claim 5 (Previously Presented): The semiconductor memory element according to claim 1, wherein the predetermined means is a heating means.

Claim 6 (Previously Presented): The semiconductor memory element according to claim 1, wherein the predetermined means is a pressurizing means.

Claim 7 (Previously Presented): The semiconductor memory element according to claim 1, wherein the predetermined means is a light irradiation means.

Claim 8 (Previously Presented): A semiconductor memory element comprising:
a substrate;
a semiconductor circuit portion disposed on the substrate and comprising an organic semiconductor including a performance deterioration material for deteriorating a performance of the organic semiconductor after the performance deterioration is activated; and
a protection portion disposed adjacent to the semiconductor circuit portion, wherein the performance deterioration material is activated by a predetermined means.

Claim 9 (Previously Presented): A semiconductor memory element comprising:
a substrate;
a semiconductor circuit portion disposed on the substrate and comprising an organic semiconductor including a performance deterioration material for deteriorating a performance of the organic semiconductor after the performance deterioration is activated; and

a film disposed adjacent to the semiconductor circuit portion, capable of obtaining light transmissive property due to an irradiation of light having a predetermined wavelength thereon, wherein

the performance deterioration material is activated by a predetermined means.

Claim 10 (Previously Presented): A semiconductor memory element comprising:

a substrate;

a semiconductor circuit portion disposed on the substrate and comprising an organic semiconductor including a performance deterioration material for deteriorating a performance of the organic semiconductor after the performance deterioration is activated;

a protection portion disposed adjacent to the semiconductor circuit portion and including a window portion; and

a seal member for sealing the window portion of the protection portion.

Claim 11 (Previously Presented): The semiconductor memory element according to claim 8, wherein

the performance deterioration material is encapsulated.

Claim 12 (Previously Presented): The semiconductor memory element according to claim 8, wherein

the predetermined means is a pressurizing means.

Claim 13 (Previously Presented): The semiconductor memory element according to claim 8, wherein

the predetermined means is a heating means.

Claim 14 (Original): The semiconductor memory element according to claim 9, wherein the predetermined means is an UV irradiation means.

Claim 15 (Original): The semiconductor memory element according to claim 9, wherein

the predetermined means is an electron beam irradiation means.

Claim 16 (Previously Presented): The semiconductor memory element according to claim 2, wherein

the deterioration in the semiconductor circuit portion of the organic semiconductor is started by stripping off the seal member.

Claim 17 (Previously Presented): The semiconductor memory element according to claim 1, wherein

the semiconductor portion is a semiconductor portion in a range corresponding to a predetermined circuit portion of the semiconductor circuit portion.

Claim 18 (Original): The semiconductor memory element according to claim 17, wherein

the predetermined circuit portion is a data area.

Claim 19 (Original): The semiconductor memory element according to claim 17, wherein

the predetermined circuit portion is a management information area.

Claim 20 (Original): The semiconductor memory element according to claim 17, wherein

the predetermined circuit portion is an electric power shutdown switch.

Claim 21 (Original): The semiconductor memory element according to claim 17, wherein

the predetermined circuit portion is an encryption key record area.

Claims 22-24 (Canceled).

Claim 25 (Previously Presented): The semiconductor memory element according to claim 3, wherein the predetermined means is a mechanical punch means.

Claim 26 (Previously Presented): The semiconductor memory element according to claim 3, wherein the predetermined means is a heating means.

Claim 27 (Previously Presented): The semiconductor memory element according to claim 3, wherein the predetermined means is a pressurizing means.

Claim 28 (Previously Presented): The semiconductor memory element according to claim 3, wherein the predetermined means is a light irradiation means.

Claim 29 (Previously Presented): The semiconductor memory element according to claim 9, wherein
the performance deterioration material is encapsulated.

Claim 30 (Previously Presented): The semiconductor memory element according to claim 10, wherein
the performance deterioration material is encapsulated.

Claim 31 (Previously Presented): The semiconductor memory element according to claim 9, wherein
the predetermined means is a pressurizing means.

Claim 32 (Previously Presented): The semiconductor memory element according to claim 9, wherein
the predetermined means is a heating means.

Claim 33 (Previously Presented): The semiconductor memory element according to claim 10, wherein

the deterioration in the semiconductor circuit portion of the organic semiconductor is started by stripping off the seal member.

Claim 34 (Previously Presented): The semiconductor memory element according to claim 2, wherein

the semiconductor portion is a semiconductor portion in a range corresponding to a predetermined circuit portion of the semiconductor circuit portion.

Claim 35 (Previously Presented): The semiconductor memory element according to claim 3, wherein

the semiconductor portion is a semiconductor portion in a range corresponding to a predetermined circuit portion of the semiconductor circuit portion.

Claim 36 (Previously Presented): The semiconductor memory element according to claim 8, wherein

the semiconductor portion is a semiconductor portion in a range corresponding to a predetermined circuit portion of the semiconductor circuit portion.

Claim 37 (Previously Presented): The semiconductor memory element according to claim 9, wherein

the semiconductor portion is a semiconductor portion in a range corresponding to a predetermined circuit portion of the semiconductor circuit portion.

Claim 38 (Previously Presented): The semiconductor memory element according to claim 10, wherein

the semiconductor portion is a semiconductor portion in a range corresponding to a predetermined circuit portion of the semiconductor circuit portion.

Claim 39 (Previously Presented): The semiconductor memory element according to claim 34, wherein

the predetermined circuit portion is a data area.

Claim 40 (Previously Presented): The semiconductor memory element according to claim 35, wherein
the predetermined circuit portion is a data area.

Claim 41 (Previously Presented): The semiconductor memory element according to claim 36, wherein
the predetermined circuit portion is a data area.

Claim 42 (Previously Presented): The semiconductor memory element according to claim 37, wherein
the predetermined circuit portion is a data area.

Claim 43 (Previously Presented): The semiconductor memory element according to claim 38, wherein
the predetermined circuit portion is a data area.

Claim 44 (Previously Presented): The semiconductor memory element according to claim 34, wherein
the predetermined circuit portion is a management information area.

Claim 45 (Previously Presented): The semiconductor memory element according to claim 35, wherein
the predetermined circuit portion is a management information area.

Claim 46 (Previously Presented): The semiconductor memory element according to claim 36, wherein
the predetermined circuit portion is a management information area.

Claim 47 (Previously Presented): The semiconductor memory element according to claim 37, wherein
the predetermined circuit portion is a management information area.

Claim 48 (Previously Presented): The semiconductor memory element according to claim 38, wherein
the predetermined circuit portion is a management information area.

Claim 49 (Previously Presented): The semiconductor memory element according to claim 34, wherein
the predetermined circuit portion is an electric power shutdown switch.

Claim 50 (Previously Presented): The semiconductor memory element according to claim 35, wherein
the predetermined circuit portion is an electric power shutdown switch.

Claim 51 (Previously Presented): The semiconductor memory element according to claim 36, wherein
the predetermined circuit portion is an electric power shutdown switch.

Claim 52 (Previously Presented): The semiconductor memory element according to claim 37, wherein
the predetermined circuit portion is an electric power shutdown switch.

Claim 53 (Previously Presented): The semiconductor memory element according to claim 38, wherein
the predetermined circuit portion is an electric power shutdown switch.

Claim 54 (Previously Presented): The semiconductor memory element according to claim 34, wherein

the predetermined circuit portion is an encryption key record area.

Claim 55 (Previously Presented): The semiconductor memory element according to claim 35, wherein

the predetermined circuit portion is an encryption key record area.

Claim 56 (Previously Presented): The semiconductor memory element according to claim 36, wherein

the predetermined circuit portion is an encryption key record area.

Claim 57 (Previously Presented): The semiconductor memory element according to claim 37, wherein

the predetermined circuit portion is an encryption key record area.

Claim 58 (Previously Presented): The semiconductor memory element according to claim 38, wherein

the predetermined circuit portion is an encryption key record area.

Claim 59 (Previously Presented): A record medium comprising a semiconductor memory element, wherein

the semiconductor memory element comprises a substrate; a semiconductor circuit portion made of an organic semiconductor disposed on the substrate; and a protection circuit disposed adjacent to the semiconductor circuit portion, the protection portion being made of a material in which a crack extending to the semiconductor circuit portion is formed after a predetermined means performs.

Claim 60 (Previously Presented): A record medium comprising a semiconductor memory element, wherein

the semiconductor memory element comprises a substrate; a semiconductor circuit portion comprising an organic semiconductor disposed on the substrate; a protection portion

disposed adjacent to the semiconductor circuit portion and including a window portion; and a strippable seal member for sealing the window portion of the protection portion.

Claim 61 (Previously Presented): A record medium comprising a semiconductor memory element, wherein

the semiconductor memory element comprises a substrate; a semiconductor circuit portion made of an organic semiconductor disposed on the substrate; a protection portion disposed adjacent to the semiconductor circuit portion; and a performance deterioration portion including a performance deterioration material for deteriorating a performance of the organic semiconductor and disposed adjacent to the protection portion, the protection portion being made of a material in which a crack extending to the semiconductor circuit portion is formed after a predetermined means performs.

Claim 62 (Previously Presented): A record medium comprising a semiconductor memory element, wherein

the semiconductor memory element comprising a substrate; a semiconductor circuit portion disposed on the substrate and made of an organic semiconductor including a performance deterioration material for deteriorating a performance of the organic semiconductor after the performance deterioration is activated; and a protection portion disposed adjacent to the semiconductor circuit portion, the performance deterioration material being activated by a predetermined means.

Claim 63 (Previously Presented): A record medium comprising a semiconductor memory element, wherein

the semiconductor memory element comprises a substrate; a semiconductor circuit portion disposed on the substrate and made of an organic semiconductor including a performance deterioration material for deteriorating a performance of the organic semiconductor after the performance deterioration is activated; and a film disposed adjacent to the semiconductor circuit portion, capable of obtaining light transmissive property due to an irradiation of light having a

predetermined wavelength thereon, the performance deterioration material being activated by a predetermined means.

Claim 64 (Previously Presented): A record medium comprising a semiconductor memory element, wherein

the semiconductor memory element comprises a substrate; a semiconductor circuit portion disposed on the substrate and made of an organic semiconductor including a performance deterioration material for deteriorating a performance of the organic semiconductor after the performance deterioration is activated; a protection portion disposed adjacent to the semiconductor circuit portion and having a window portion; and a strippable seal member for sealing the window portion of the protection portion.

Claims 65-67 (Canceled).